



**Product data sheet** 

#### **1. General description**

Ultrafast power diode in a SMB surface-mountable plastic package.

#### 2. Features and benefits

- Low on-state loss
- Low leakage current
- Low thermal resistance
- Surface-mountable package
- Reduces switching losses in associated MOSFET or IGBT

#### 3. Applications

- Buck and Boost converter
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- Inverter freewheeling and protection diode

# 4. Quick reference data

uick reference data						
Parameter	Conditions	Values				Unit
e maximum rating						
repetitive peak reverse voltage		600			V	
average forward current	δ = 0.5 ; square-wave pulse; T <sub>lead</sub> ≤ 105 °C; Fig. 1; Fig. 2; Fig. 3	3			A	
repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>lead</sub> ≤ 105 °C; square-wave pulse	6			A	
non-repetitive peak forward current	$t_{\rm p}$ = 10 ms; $T_{\rm j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100			A	
	$t_{\rm p}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse;		1	10		А
Parameter	Conditions		Min	Тур	Max	Unit
aracteristics						
forward voltage	I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	-	1.3	V
	I <sub>F</sub> = 3 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	0.88	1.05	V
characteristics		1	1	1	1	
reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 50 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>		-	50	-	ns
	<ul> <li>maximum rating</li> <li>repetitive peak reverse voltage</li> <li>average forward current</li> <li>repetitive peak forward current</li> <li>non-repetitive peak forward current</li> <li>Parameter</li> <li>aracteristics</li> <li>forward voltage</li> <li>characteristics</li> </ul>	ParameterConditionsmaximum ratingrepetitive peak reverse voltageaverage forward current $\delta = 0.5$ ; square-wave pulse; $T_{lead} \le 105 ^{\circ}$ C; Fig. 1; Fig. 2; Fig. 3repetitive peak forward current $\delta = 0.5$ ; $t_p = 25 \mu$ s; $T_{lead} \le 105 ^{\circ}$ C; square-wave pulsenon-repetitive peak forward current $\delta = 0.5$ ; $t_p = 25 \mu$ s; $T_{lead} \le 105 ^{\circ}$ C; square-wave pulsenon-repetitive peak forward current $t_p = 10 \text{ms}$ ; $T_{j(init)} = 25 ^{\circ}$ C; sine-wave pulse; Fig. 4 $t_p = 8.3 \text{ms}$ ; $T_{j(init)} = 25 ^{\circ}$ C; sine-wave pulse;ParameterConditionsaracteristics $I_F = 3 \text{A}$ ; $T_j = 25 ^{\circ}$ C; Fig. 6 $I_F = 3 \text{A}$ ; $T_j = 150 ^{\circ}$ C; Fig. 6forward voltage $I_F = 3 \text{A}$ ; $T_j = 150 ^{\circ}$ C; Fig. 6there is the server of the serv	ParameterConditionsmaximum ratingrepetitive peak reverse voltage $\delta = 0.5$ ; square-wave pulse; $T_{lead} \le 105 ^{\circ}$ C; Fig. 1; Fig. 2; Fig. 3average forward current $\delta = 0.5$ ; square-wave pulse; $T_{lead} \le 105 ^{\circ}$ C; Fig. 1; Fig. 2; Fig. 3repetitive peak forward current $\delta = 0.5$ ; $t_p = 25 \mu$ s; $T_{lead} \le 105 ^{\circ}$ C; square-wave pulsenon-repetitive peak forward current $\delta = 0.5$ ; $t_p = 25 \mu$ s; $T_{lead} \le 105 ^{\circ}$ C; square-wave pulsenon-repetitive peak forward current $t_p = 10 \mathrm{ms}$ ; $T_{j(init)} = 25 ^{\circ}$ C; sine-wave pulse; Fig. 4 $t_p = 8.3 \mathrm{ms}$ ; $T_{j(init)} = 25 ^{\circ}$ C; sine-wave pulse;ParameterConditionsaracteristicsI_F = 3 A; T_j = 25 ^{\circ}C; Fig. 6 I_F = 3 A; T_j = 150 ^{\circ}C; Fig. 6characteristicsI_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/\mus;	ParameterConditionsValmaximum ratingrepetitive peak reverse voltage $\delta = 0.5$ ; square-wave pulse; $T_{iead} \le 105 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 36average forward current $\delta = 0.5$ ; square-wave pulse; $T_{iead} \le 105 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 37repetitive peak forward current $\delta = 0.5$ ; $t_p = 25 \ \mu s$ ; $T_{iead} \le 105 \text{ °C}$ ; square-wave pulse1non-repetitive peak forward current $\delta = 0.5$ ; $t_p = 25 \ \mu s$ ; $T_{iead} \le 105 \text{ °C}$ ; square-wave pulse1non-repetitive peak forward current $t_p = 10 \ m s$ ; $T_{j(init)} = 25 \ ^{\circ}C$ ; sine-wave pulse; Fig. 41 <b>ParameterConditionsMinaracteristics</b> I I_F = 3 A; T_j = 25 \ ^{\circ}C; Fig. 6-forward voltageI_F = 3 A; T_j = 25 \ ^{\circ}C; Fig. 6-I_F = 3 A; T_j = 150 \ ^{\circ}C; Fig. 6 <b>characteristics</b> I I_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/\mus;-	ParameterConditionsValuese maximum ratingrepetitive peak reverse voltage $600$ average forward current $\delta = 0.5$ ; square-wave pulse; $T_{lead} \le 105$ °C; Fig. 1; Fig. 2; Fig. 3 $600$ average forward current $\delta = 0.5$ ; square-wave pulse; $T_{lead} \le 105$ °C; square-wave pulse $3$ repetitive peak forward current $\delta = 0.5$ ; $t_p = 25 \ \mu s$ ; $T_{lead} \le 105$ °C; square-wave pulse $6$ non-repetitive peak forward current $t_p = 10 \ ms$ ; $T_{j(nit)} = 25 \ ^{\circ}C$ ; sine-wave pulse; $Fig. 4$ $100$ ParameterConditionsMinTyparacteristics $I_F = 3 \ A$ ; $T_j = 25 \ ^{\circ}C$ ; Fig. 6 $ -$ forward voltage $I_F = 3 \ A$ ; $T_j = 150 \ ^{\circ}C$ ; Fig. 6 $ -$ there is the second pulse $ 0.88$ characteristics $I_F = 1 \ A$ ; $V_R = 30 \ V$ ; $dI_F/dt = 50 \ A/\mu s$ ; $ 50$	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Values \\ \hline maximum rating \\ \hline repetitive peak reverse voltage & $600$ \\ \hline average forward current & $\delta = 0.5$; square-wave pulse; $T_{lead} \le 105 ^{\circ}C$; $$ $3$ \\ \hline repetitive peak forward current & $\delta = 0.5$; t_p = 25 $\mu$; $T_{lead} \le 105 ^{\circ}C$; $$ $6$ \\ \hline current & $\delta = 0.5$; t_p = 25 $\mu$; $T_{lead} \le 105 ^{\circ}C$; $$ $6$ \\ \hline current & $t_p = 10$ ms; $T_{j(nit)} = 25 ^{\circ}C$; sine-wave pulse; $$ $100$ \\ \hline repetitive peak forward current & $t_p = 10$ ms; $T_{j(nit)} = 25 ^{\circ}C$; sine-wave pulse; $$ $100$ \\ \hline example & $t_p = 8.3$ ms; $T_{j(nit)} = 25 ^{\circ}C$; sine-wave pulse; $$ $110$ \\ \hline example & $t_p = 3$ A$; $T_j = 25 ^{\circ}C$; $fig. 6$ $$ $-$ $$ $-$ $$ $1.3$ \\ \hline reverse recovery time $$ $I_F = 1$ $A$; $V_R = 30$ $V$; $dI_F/dt = 50$ $A/$\mu$; $$ $-$ $50$ $$ $-$ $ $$ $50$ $$ $-$ $$ $$ $50$ $$ $-$ $$ $$ $50$ $$ $-$ $$ $$ $50$ $$ $-$ $$ $$ $$ $50$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$

## 5. Pinning information

Table 2. Pinning information							
Symbol	Description	Simplified outline	Graphic symbol				
K	cathode		K LA A				
А	anode	1 2	K — A 001aaa020				
	Symbol K	Symbol         Description           K         cathode	Symbol         Description         Simplified outline           K         cathode				

## 6. Ordering information

Table 3. Ordering information							
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	• •	Package issue date	
MURS360B	SMB	MURS360BJ	Reel	3000	SMB	20-Feb-2017	

### 7. Marking

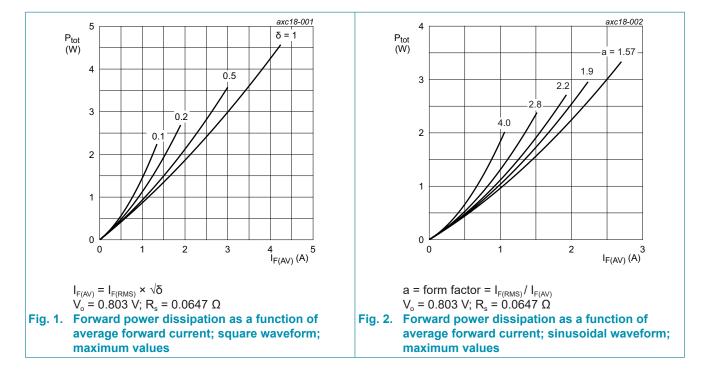
Table 4. Marking codes						
Type number	Marking codes					
MURS360B	360B					

#### 8. Limiting values

#### Table 5. Limiting values

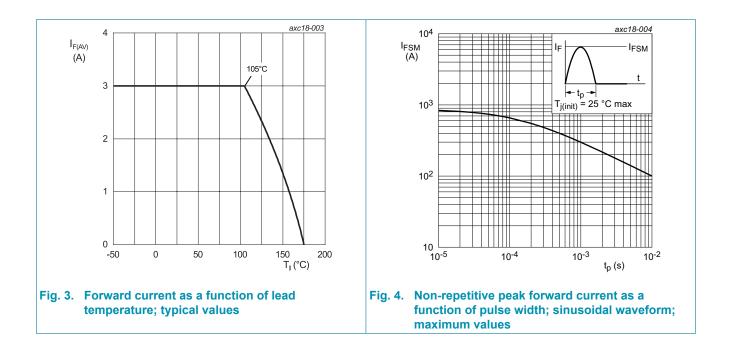
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		600	V
$V_{\text{RWM}}$	crest working reverse voltage		600	V
V <sub>R</sub>	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T <sub>lead</sub> ≤ 105 °C; Fig. 1; Fig. 2; Fig. 3	3	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>lead</sub> ≤ 105 °C; square-wave pulse	6	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	100	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	110	А
T <sub>stg</sub>	storage temperature		-65 to 175	°C
Tj	junction temperature		175	°C



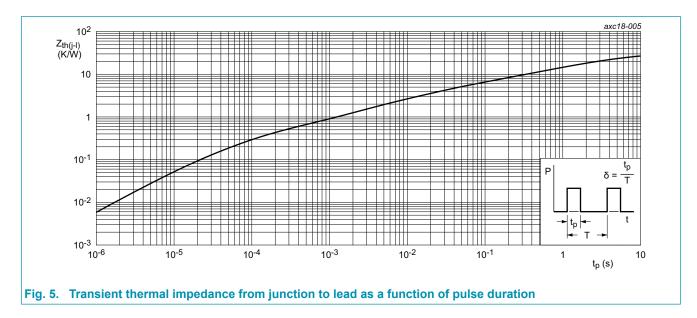
Ultrafast power diode

**MURS360B** 



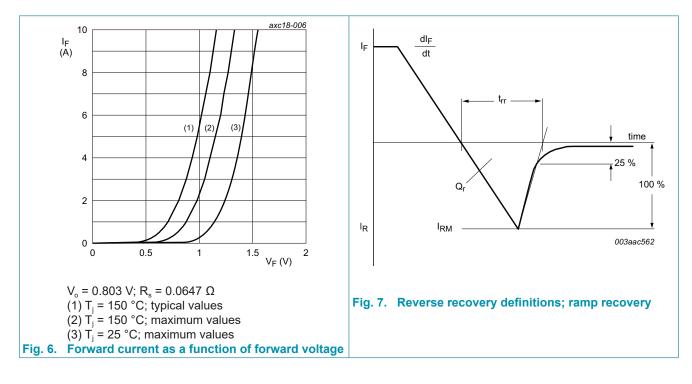
### 9. Thermal characteristics

Table 6. Th	ermal characteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	mounted on a minimum footprint printed-circuit board (FR4); <u>Fig. 5</u>	-	23	25	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	mounted on a minimum footprint printed-circuit board (FR4)	-	75	-	K/W



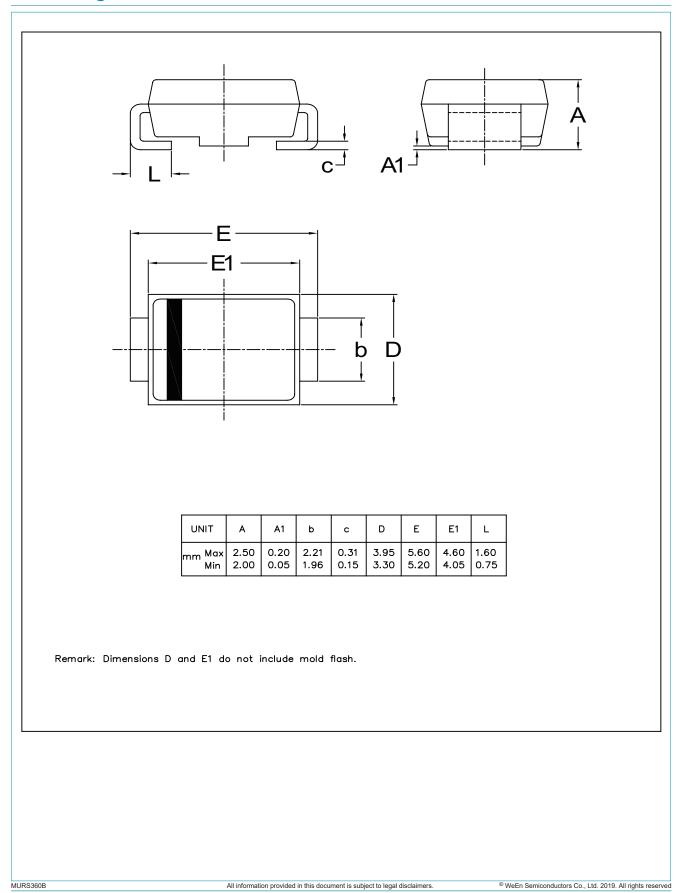
#### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics					
V <sub>F</sub>	forward current	I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	-	1.3	V
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.88	1.05	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	3	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	1	mA
Dynamic	characteristics	· · · · ·	I			
Q <sub>r</sub> reverse charge	reverse charge	$I_F = 3 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	122	-	nC
		$I_F = 3 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	199	-	nC
t <sub>rr</sub> reverse	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	50	-	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ Step recovery}$	-	-	50	ns
		$I_F = 3 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	52	-	ns
		$I_F = 3 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	65	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 3 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	4.7	-	A
		$I_F = 3 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	6.1	-	A
E <sub>as</sub>	non-repetitive avalanche energy	I <sub>R</sub> = 1.2 A; T <sub>j(init)</sub> = 25 °C; L = 15 mH	10.8	-	-	mJ



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## 11. Package outline



# MURS360B

#### Ultrafast power diode

#### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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